

### isc N-Channel MOSFET Transistor

# IRFB4019, IIRFB4019

#### • FEATURES

- Static drain-source on-resistance:
  R<sub>DS</sub>(on) ≤95mΩ
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRITION

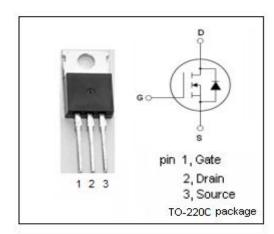
• 175℃ operating junction temperature and repetitive avalanche capability

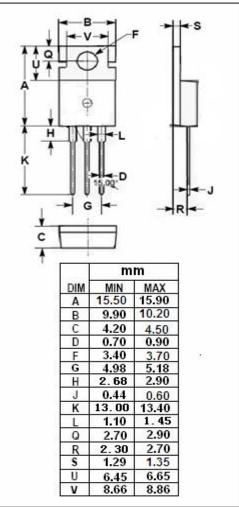
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	150	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Drain Current-Continuous	17	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	51	А	
$P_D$	Total Dissipation @T <sub>C</sub> =25℃	80	W	
Tj	Max. Operating Junction Temperature 175		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature	-55~175	$^{\circ}$	

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	1.88	°C/W	
Rth(ch-a)	Channel-to-ambient thermal resistance	62	°C/W	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	150			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =50 μ A	3		4.9	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =10A			95	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =150V; V <sub>GS</sub> = 0V			20	μА
V <sub>SD</sub>	Diode forward voltage	Is=10A; V <sub>GS</sub> = 0V			1.3	V

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